

Standard Recovery Diodes (Stud Version), 6 A



DO-203AA (DO-4)

FEATURES

- High surge current capability
- Avalanche types available
- Stud cathode and stud anode version
- Wide current range
- Types up to 1200 V V_{RRM}
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912


RoHS
COMPLIANT

TYPICAL APPLICATIONS

- Converters
- Power supplies
- Machine tool controls
- Battery charges

PRODUCT SUMMARY

$I_{F(AV)}$	6 A
Package	DO-203AA (DO-4)
Circuit configuration	Single diode

MAJOR RATINGS AND CHARACTERISTICS

PARAMETER	TEST CONDITIONS	VALUES	UNITS
$I_{F(AV)}$		6	A
	T_C	160	$^{\circ}C$
$I_{F(RMS)}$		9.5	A
I_{FSM}	50 Hz	159	A
	60 Hz	167	
I^2t	50 Hz	134	A^2s
	60 Hz	141	
V_{RRM}	Range	100 to 1200	V
T_J		-65 to 175	$^{\circ}C$

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS

TYPE NUMBER	VOLTAGE CODE	V_{RRM} , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V	V_{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	$V_{R(BR)}$, MINIMUM AVALANCHE VOLTAGE V ⁽¹⁾	I_{RRM} MAXIMUM AT $T_J = 175^{\circ}C$ mA
VS-6F(R)	10	100	150	-	12
	20	200	275	-	
	40	400	500	500	
	60	600	725	750	
	80	800	950	950	
	100	1000	1200	1150	
	120	1200	1400	1350	

Note
⁽¹⁾ Avalanche version only available from V_{RRM} 400 V to 1200 V



FORWARD CONDUCTION					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum average forward current at case temperature	$I_{F(AV)}$	180° conduction, half sine wave		6	A
				160	°C
Maximum RMS forward current	$I_{F(RMS)}$			9.5	A
Maximum non-repetitive peak reverse power	$P_R^{(1)}$	10 μ s square pulse, $T_J = T_J$ maximum		4	K/W
Maximum peak, one cycle forward, non-repetitive surge current	I_{FSM}	t = 10 ms	No voltage reapplied	159	A
		t = 8.3 ms		167	
		t = 10 ms	100 % V_{RRM} reapplied	134	
		t = 8.3 ms		141	
Maximum I^2t for fusing	I^2t	t = 10 ms	No voltage reapplied	127	A ² s
		t = 8.3 ms		116	
		t = 10 ms	100 % V_{RRM} reapplied	90	
		t = 8.3 ms		82	
Maximum $I^2\sqrt{t}$ for fusing	$I^2\sqrt{t}$	t = 0.1 ms to 10 ms, no voltage reapplied		1270	A ² \sqrt{s}
Low level value of threshold voltage	$V_{F(TO)1}$	(16.7 % $\times \pi \times I_{F(AV)} < I < \pi \times I_{F(AV)}$), $T_J = T_J$ maximum		0.63	V
High level value of threshold voltage	$V_{F(TO)2}$	(I > $\pi \times I_{F(AV)}$), $T_J = T_J$ maximum		0.86	
Low level value of forward slope resistance	r_{f1}	(16.7 % $\times \pi \times I_{F(AV)} < I < \pi \times I_{F(AV)}$), $T_J = T_J$ maximum		15.7	m Ω
High level value of forward slope resistance	r_{f2}	(I > $\pi \times I_{F(AV)}$), $T_J = T_J$ maximum		5.6	
Maximum forward voltage drop	V_{FM}	$I_{pk} = 19$ A, $T_J = 25$ °C, $t_p = 400$ μ s rectangular wave		1.10	V

Note

(1) Available only for avalanche version, all other parameters the same as 6F

THERMAL AND MECHANICAL SPECIFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction temperature range	T_J		-65 to 175	°C
Maximum storage temperature range	T_{Stg}		-65 to 200	
Maximum thermal resistance, junction to case	R_{thJC}	DC operation	2.5	K/W
Maximum thermal resistance, case to heatsink	R_{thCS}	Mounting surface, smooth, flat and greased	0.5	
Mounting torque, ± 10 %		Lubricated threads (Not lubricated threads)	1.2 (1.5)	N · m (lbf · in)
Approximate weight			7	g
			0.25	oz.
Case style		See dimensions - link at the end of datasheet	DO-203AA (DO-4)	

ΔR_{thJC} CONDUCTION				
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS
180°	0.34	0.29	$T_J = T_J$ maximum	K/W
120°	0.44	0.48		
90°	0.57	0.63		
60°	0.85	0.88		
30°	1.37	1.39		

Note

• The table above shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

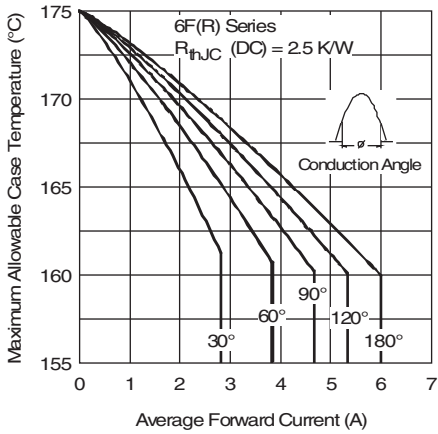


Fig. 1 - Current Ratings Characteristics

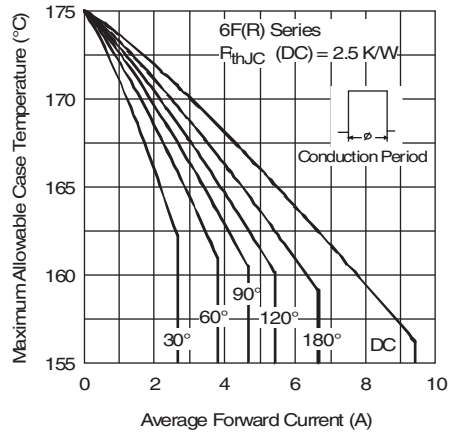


Fig. 2 - Current Ratings Characteristics

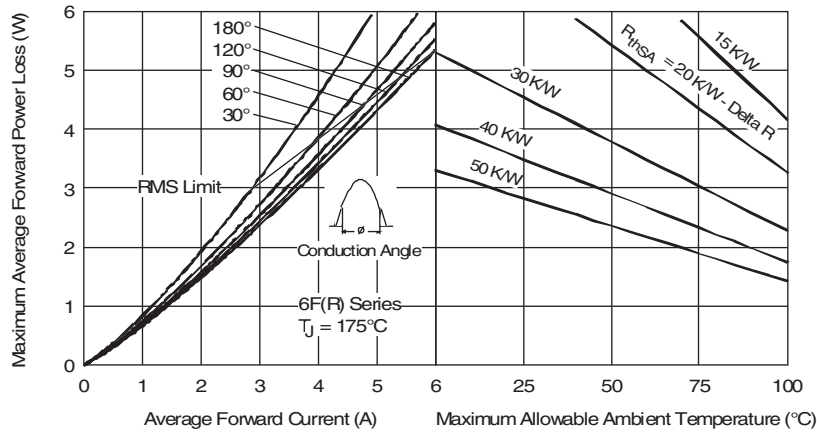


Fig. 3 - Forward Power Loss Characteristics

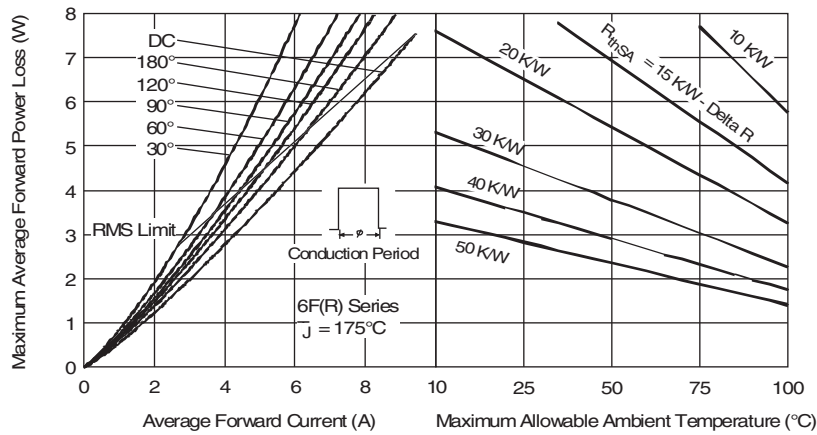


Fig. 4 - Forward Power Loss Characteristics

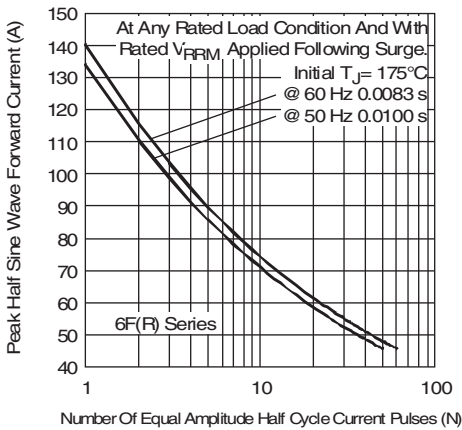


Fig. 5 - Maximum Non-Repetitive Surge Current

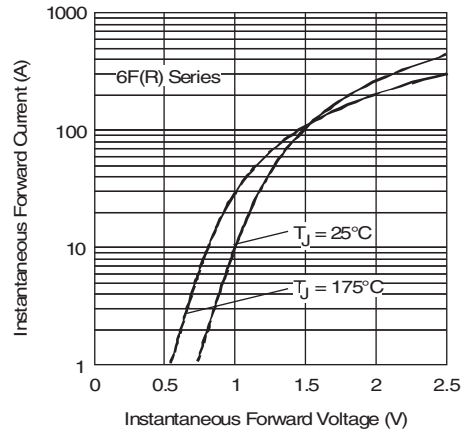


Fig. 7 - Forward Voltage Drop Characteristics

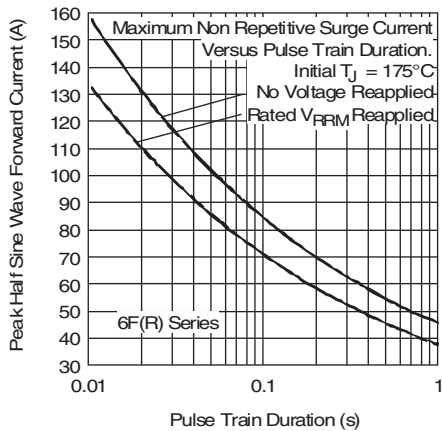


Fig. 6 - Maximum Non-Repetitive Surge Current

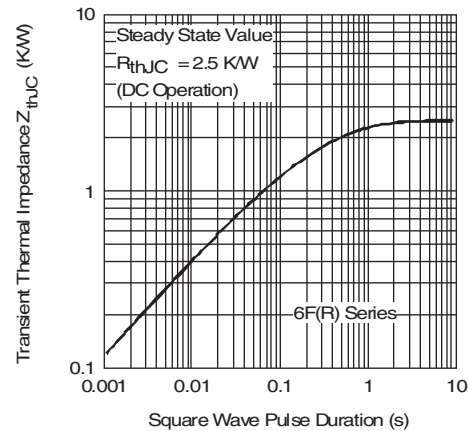


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

ORDERING INFORMATION TABLE

Device code	VS-	6	F	R	120	M
	①	②	③	④	⑤	⑥
1	-	Vishay Semiconductors product				
2	-	Current rating: Code = $I_{F(AV)}$				
3	-	F = Standard device				
4	-	<ul style="list-style-type: none"> None = Stud normal polarity (cathode to stud) R = Stud reverse polarity (anode to stud) 				
5	-	Voltage code x 10 = V_{RRM} (see Voltage Ratings table)				
6	-	<ul style="list-style-type: none"> None = Stud base DO-203AA (DO-4) 10-32UNF-2A M = Stud base DO-203AA (DO-4) M5 x 0.8 (not available for avalanche diode) 				

LINKS TO RELATED DOCUMENTS

Dimensions	www.vishay.com/doc?95311
------------	--

DO-203AA (DO-4)

DIMENSIONS in millimeters (inches)





Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and/or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

Material Category Policy

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.

Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as Halogen-Free follow Halogen-Free requirements as per JEDEC JS709A standards. Please note that some Vishay documentation may still make reference to the IEC 61249-2-21 definition. We confirm that all the products identified as being compliant to IEC 61249-2-21 conform to JEDEC JS709A standards.



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

Телефон: 8 (812) 309 58 32 (многоканальный)

Факс: 8 (812) 320-02-42

Электронная почта: org@eplast1.ru

Адрес: 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.